

PROJECT - III
EE 619A: VLSI SYSTEM DESIGN

GROUP NAME: Backbench Designers

GROUP MEMBERS:

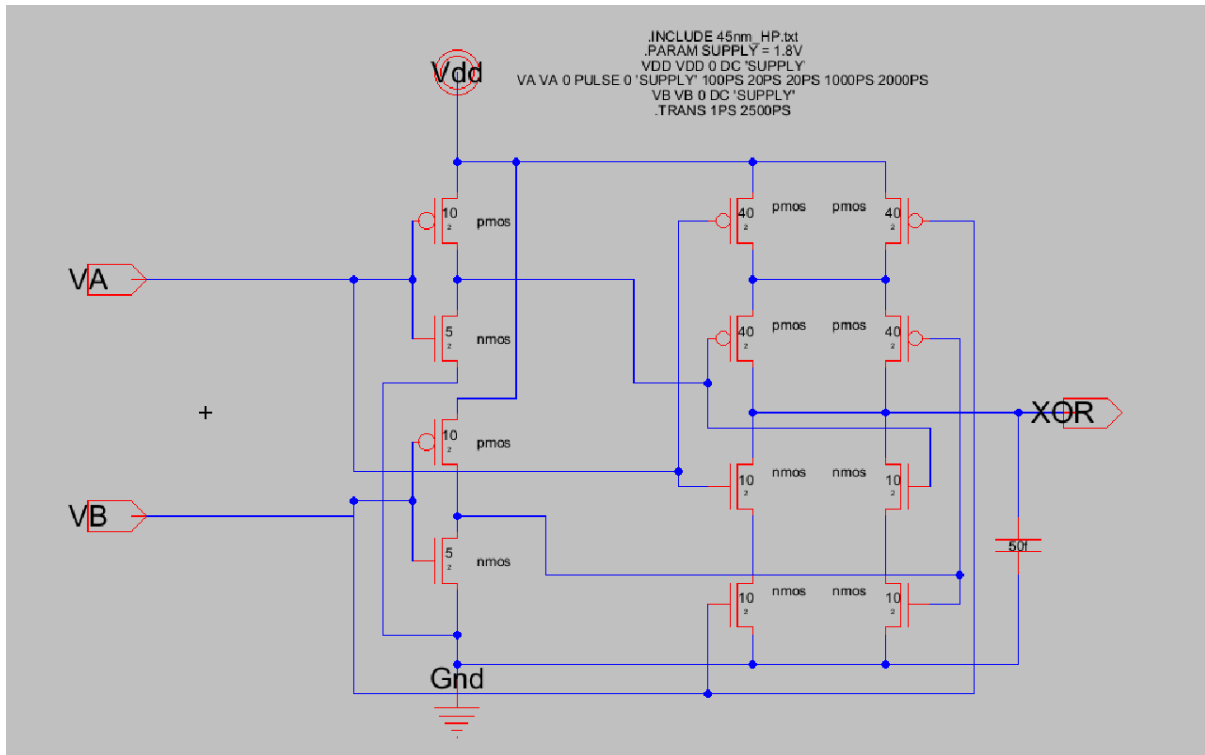
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- Bibek Lakra - 190237 - bibekp@iitk.ac.in
- N Bhuvan - 190521 - nbhuvan@iitk.ac.in

DESIGN RESPONSIBILITY:

- 2-input XOR Gate: N Bhuvan
- 2-input NAND Gate: Akshay Mehta
- 2-input NOR Gate: Bibek Lakra

First Standard Cell : 2-input XOR gate

Screenshot of the schematic:

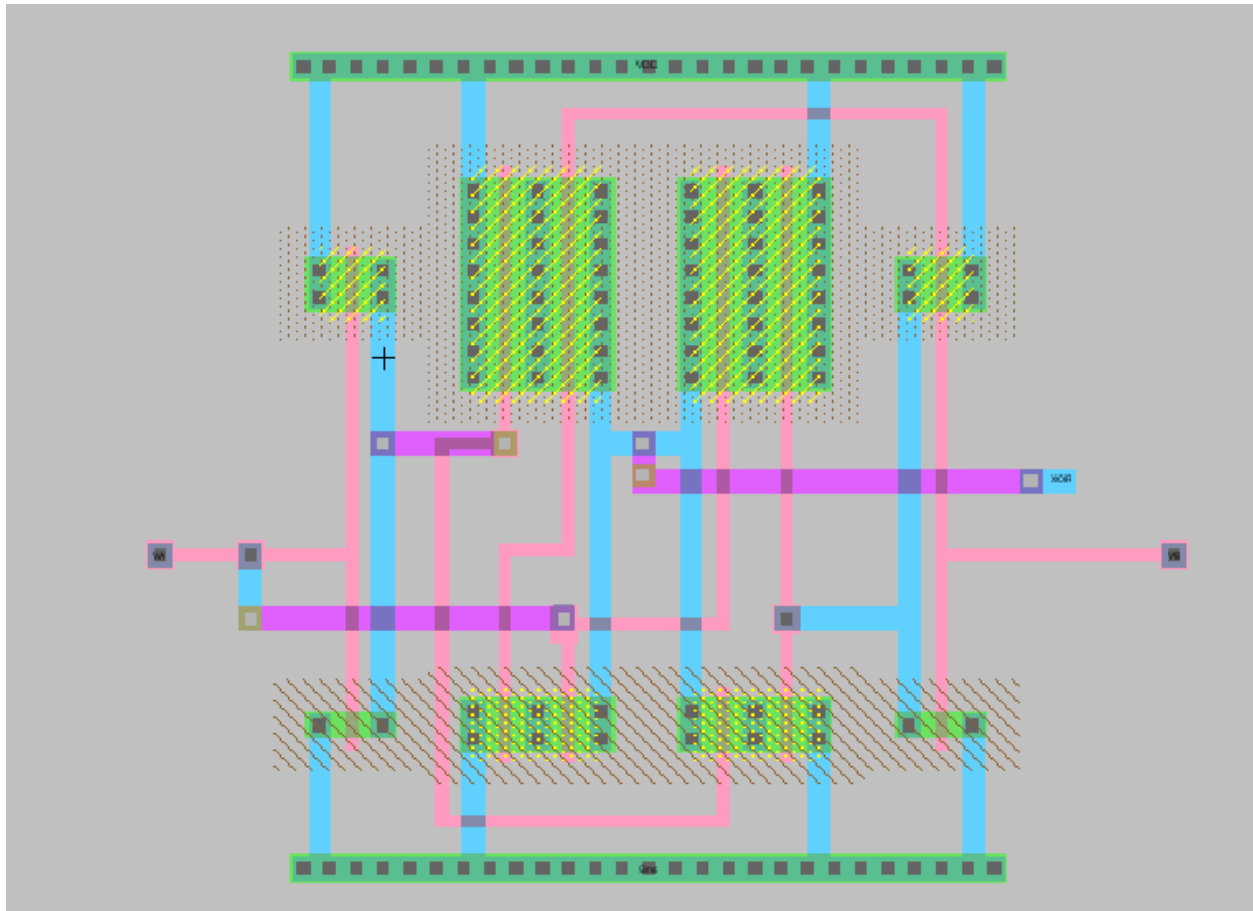


Explanation on how the transistor sizes were chosen:

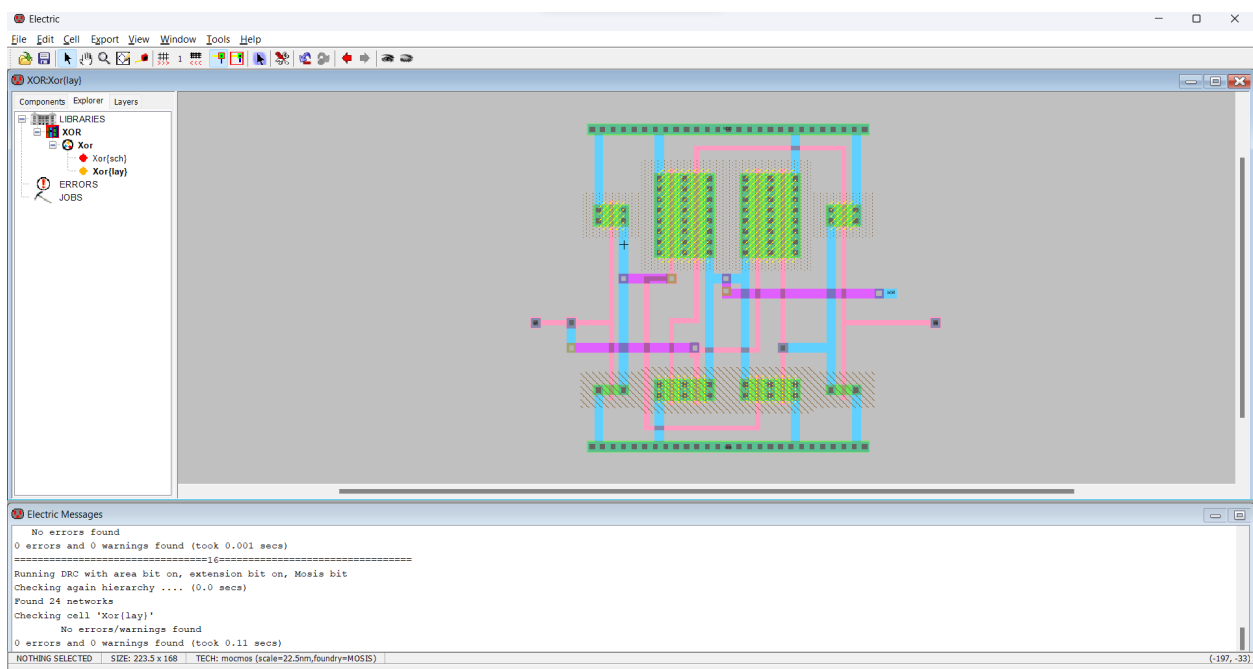
In the inverter, the PMOS is 10λ sized and NMOS transistor is 5λ sized, this we know from the standard inverter which has a $W_p:W_n = 2 : 1$ and we scaled it to 5. For XOR we first found out the schematic from taking Y' and got $Y' = (A \& B) + (A' \& B')$, from which we got the pulldown network. And then we just took the dual of this to get the pull up network.

The sizing has been done in such a way that it has the same worst case delay as that of the inverter used for getting A' and B' . Worst case delay occurs when only one series NMOS tries to pull the output. As there are two NMOS in series each should have a sizing of $2x$. And for pull up it occurs when only two PMOS tries to pull up the output, here the sizing should be $4x$. So each of the PMOS is 40λ sized and NMOS is 10λ sized.

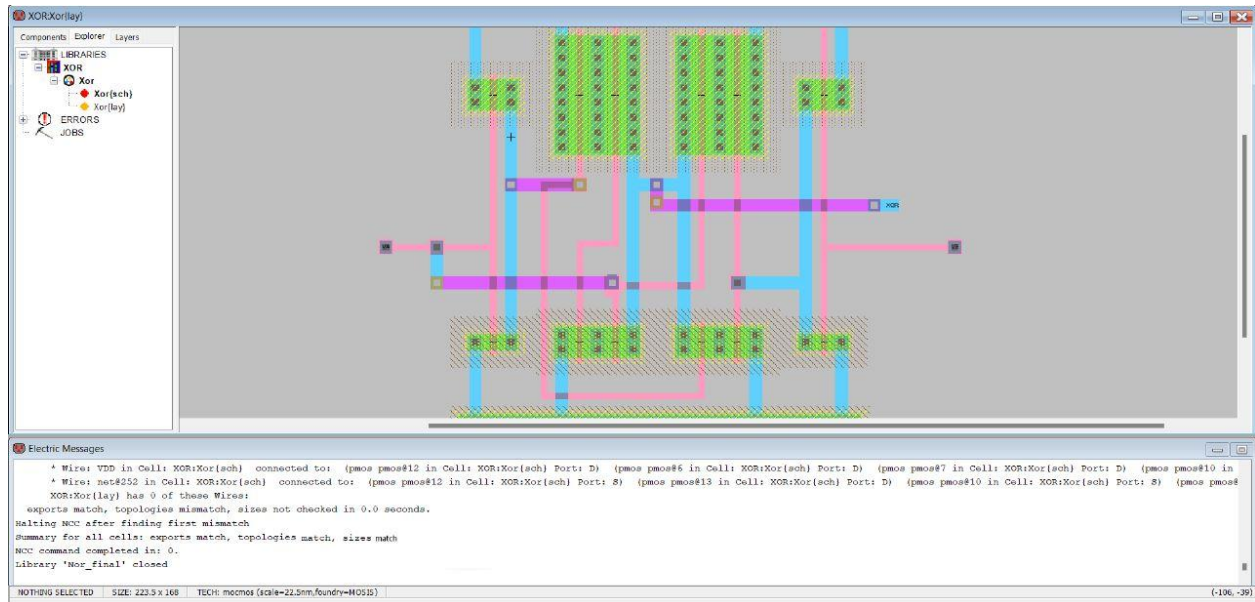
Screenshot of the Layout:



Screenshot with DRC log:



Screenshot with LVS log:



Size of Circuit = 223.5 x 168 nm

Table with the propagation delay values from the schematic and the layout for 5 fF and 50 fF fanout loads :

| Capacitor | Propagation delay(Schematic) | Propagation delay(Layout) |
|-----------|------------------------------|---------------------------|
| 5fF | 13 ps | 17ps |
| 50fF | 47ps | 17ps |

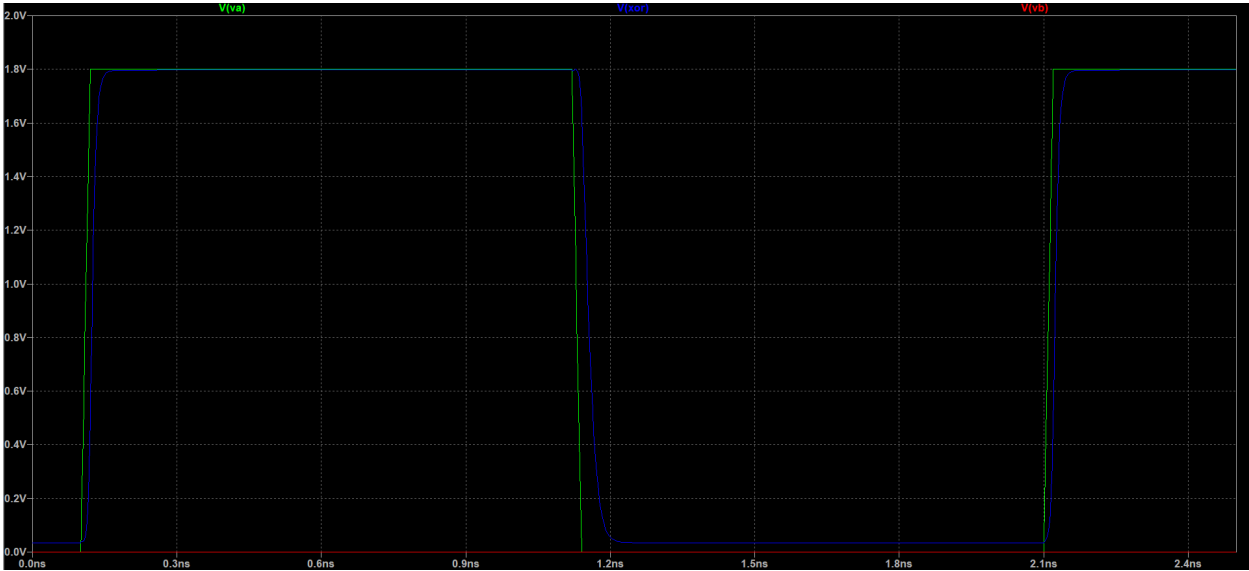
The power consumption from the schematic and layout-extracted simulations :

| Simulation | Avg Power Consumption |
|--------------------|-----------------------|
| Schematic | 1.4 mW |
| Layout - extracted | |

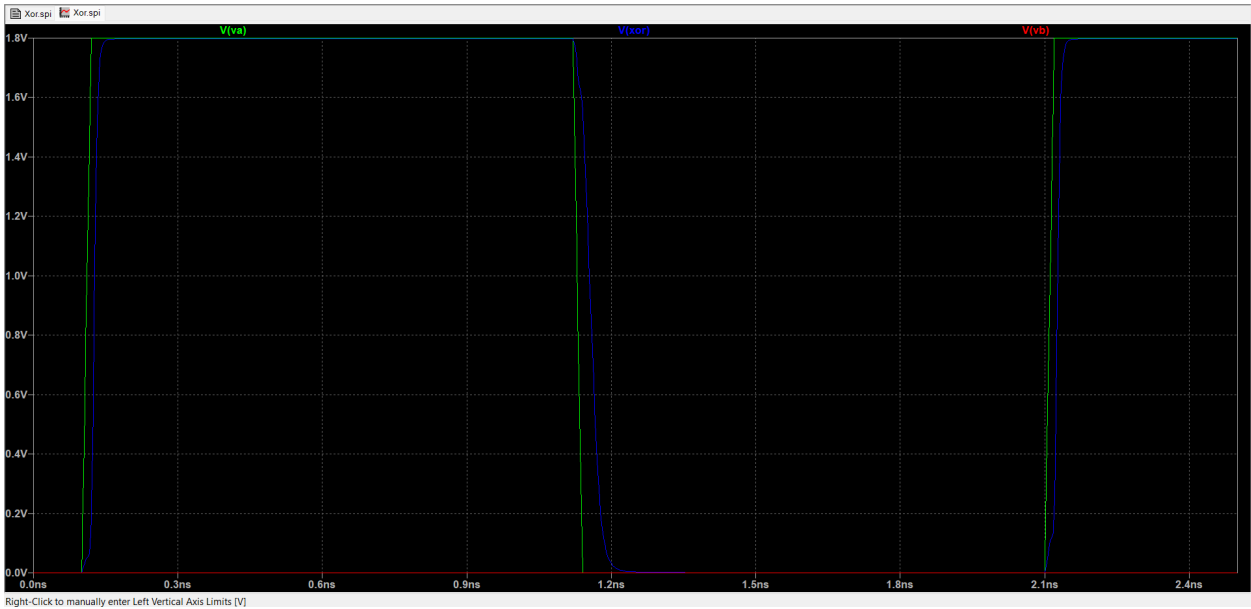
Waveform Analysis:

| A(Va) | B(Vb) | Y(Vout) |
|-------|-------|---------|
| 0 | 0 | 0 |
| 0 | 1 | 1 |
| 1 | 0 | 1 |
| 1 | 1 | 0 |

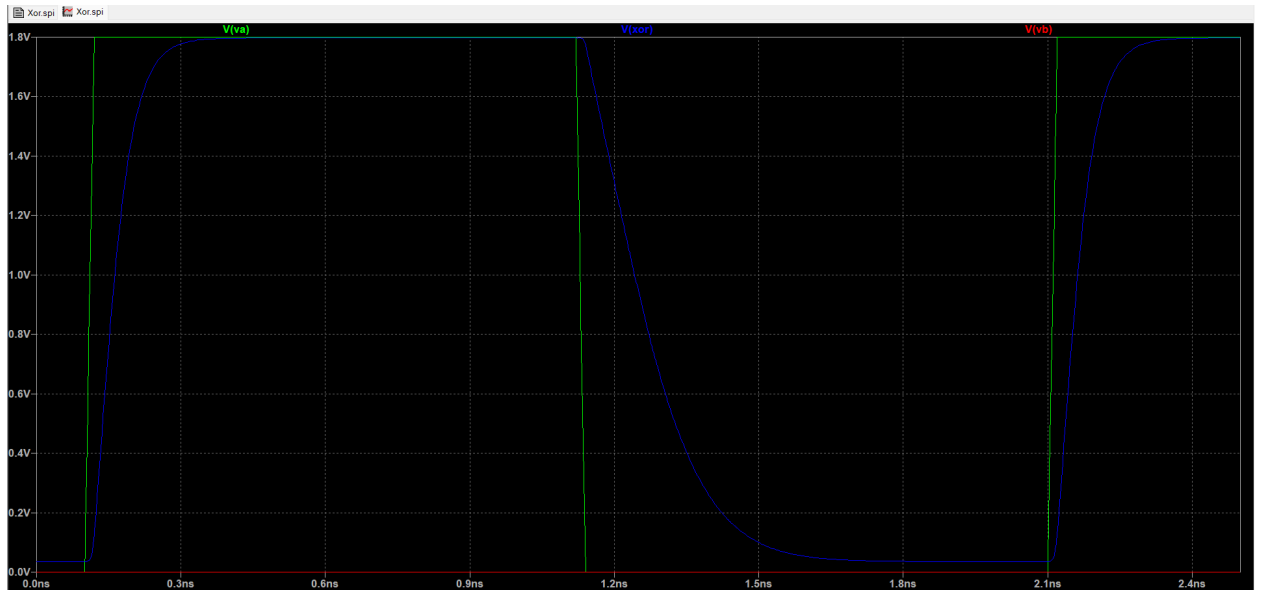
- For $C=5fF$
 - Schematic:



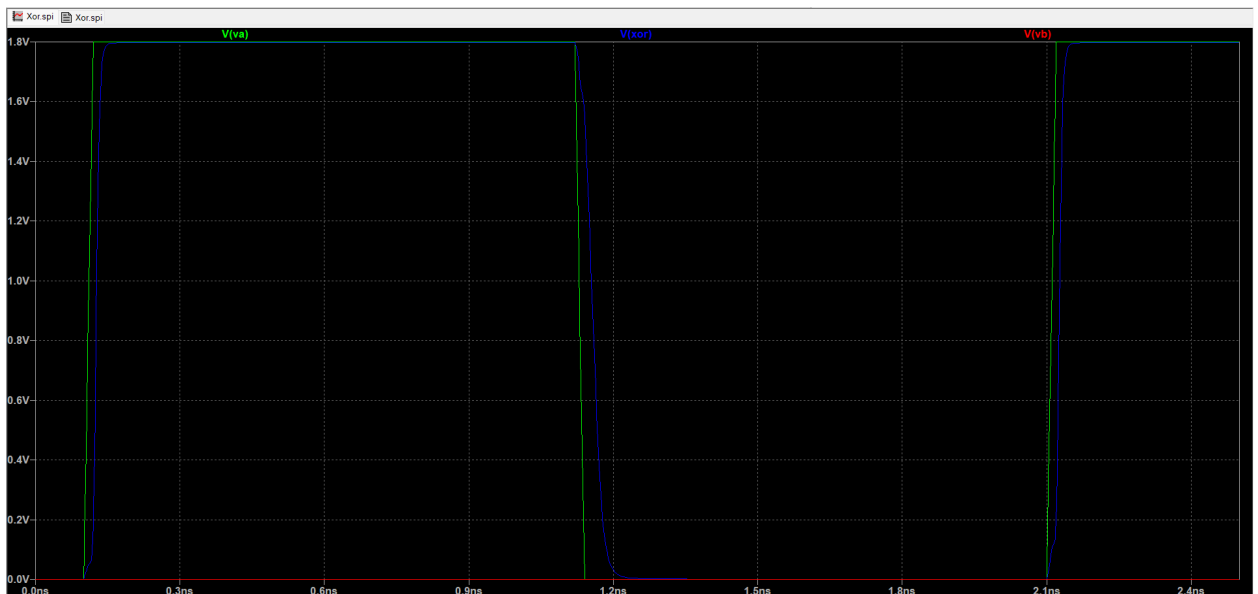
- Layout:



- Schematic:

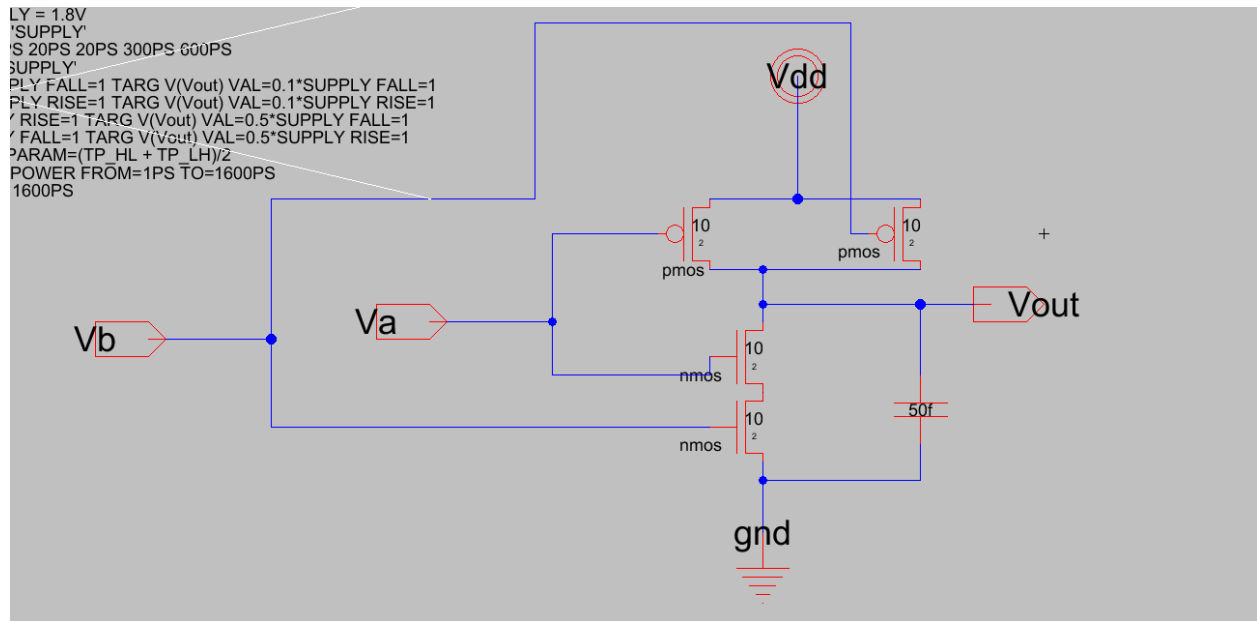


- Layout:



2. Second standard cell : 2-input NAND gate

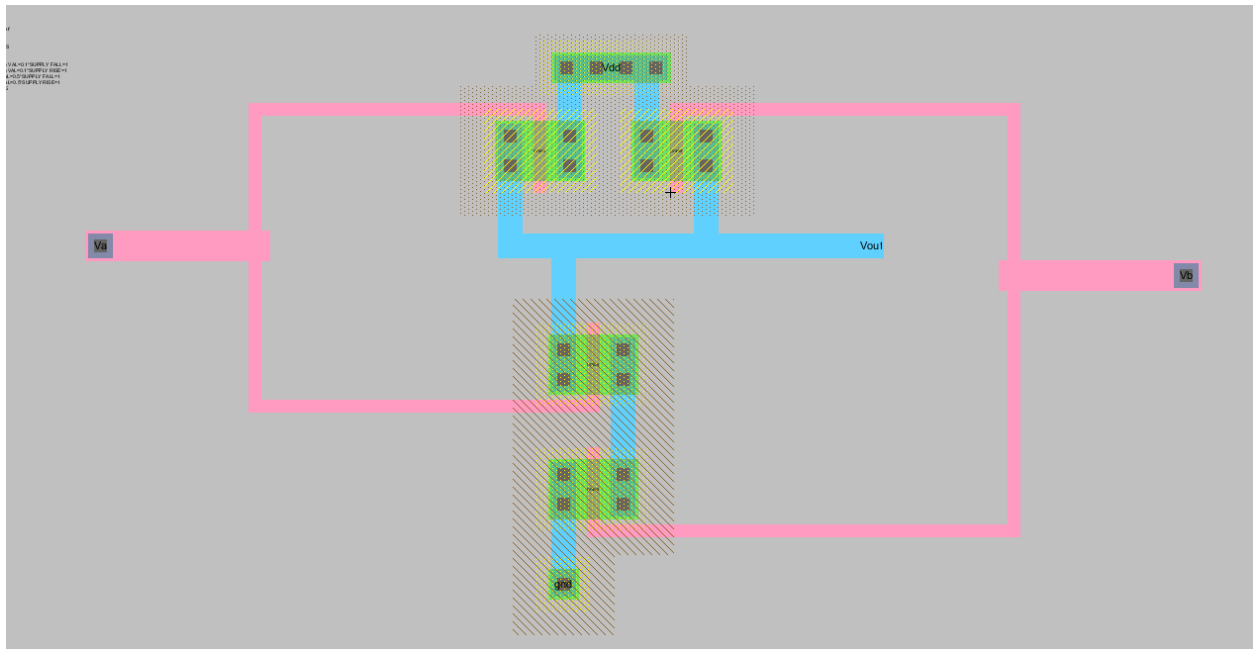
- Screenshot of the schematic



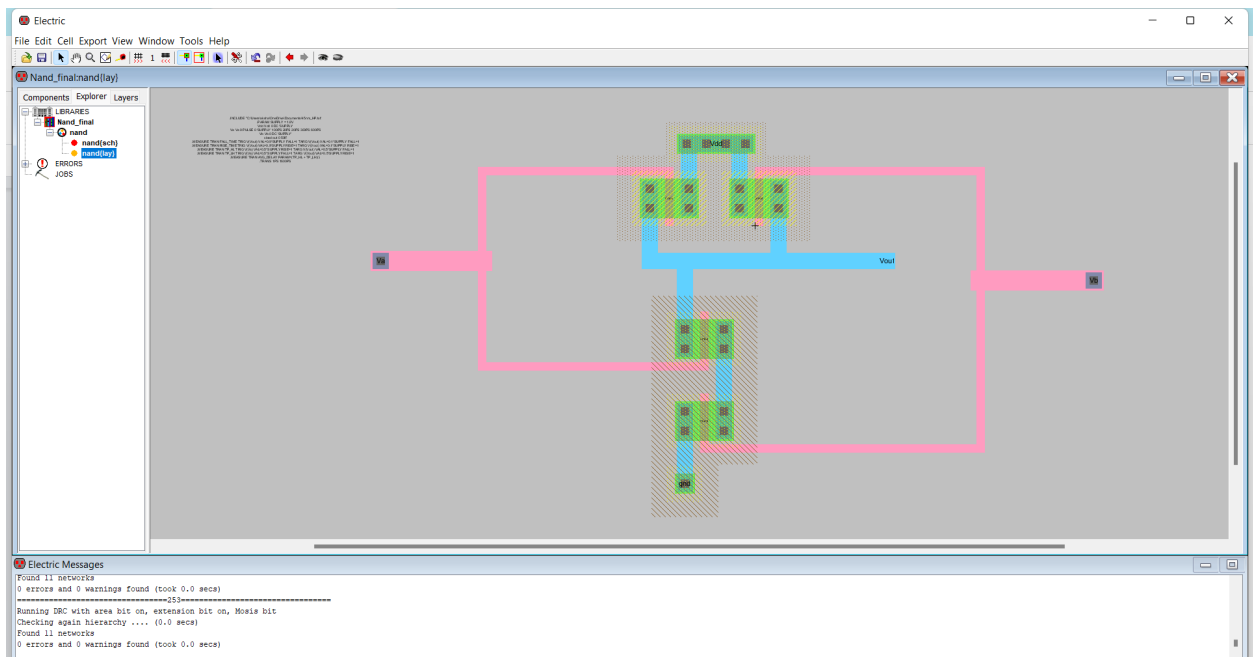
Explanation on how the transistor sizes were chosen

Here, the size of pmos is 10λ & size of nmos is 10λ . Two pmos of 10λ in parallel provide resistance equal to 10λ size pmos. Two nmos of size 10λ will provide worst-case resistance equal to that of 5λ size. If we look at final equivalent sizes, they came up to a ratio of 2:1 (PUN:PDN)

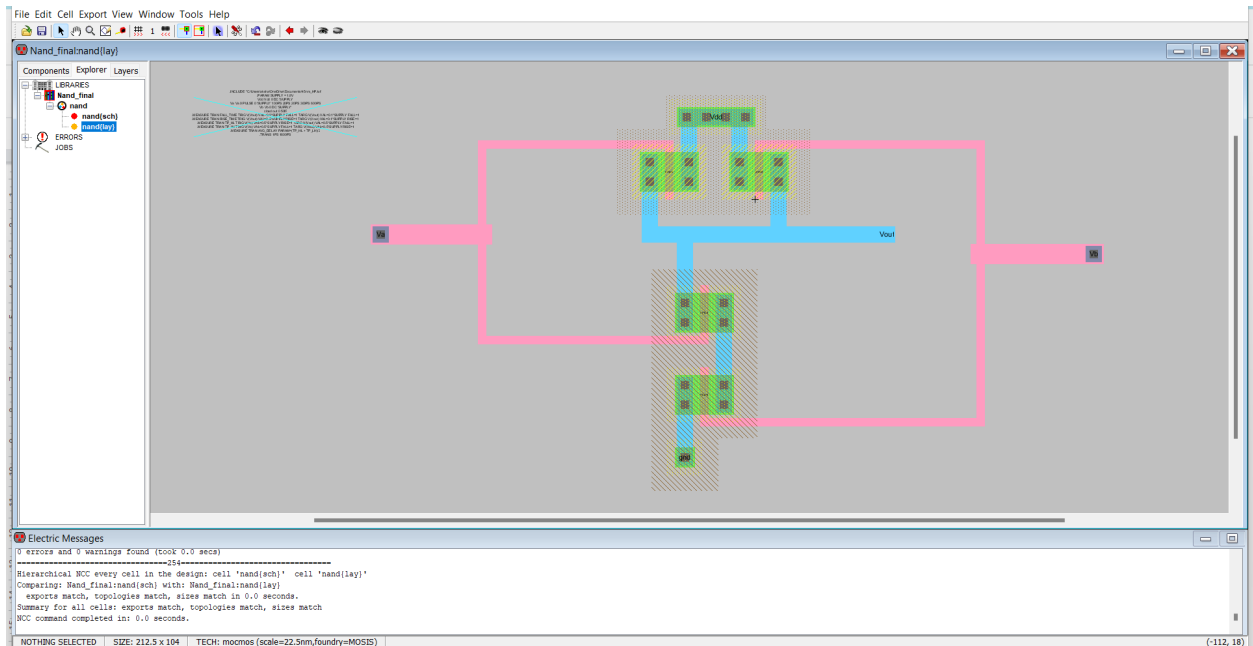
- Screenshot of Layout



- Screenshot of layout with DRC log:



- Screenshot of Layout with LVS log:



Size of Circuit = 212.5×104 nm

- Table with the propagation delay values from the schematic and the layout for 5 fF and 50 fF fanout loads :

| Capacitor | Propagation delay(Schematic) | Propagation delay(Layout) |
|-----------|------------------------------|---------------------------|
| 5fF | 1.32167e-011 s | 1.51904e-011 s |
| 50fF | 9.60035e-011 s | 9.76027e-011 s |

- the power consumption from the schematic and layout-extracted simulations :

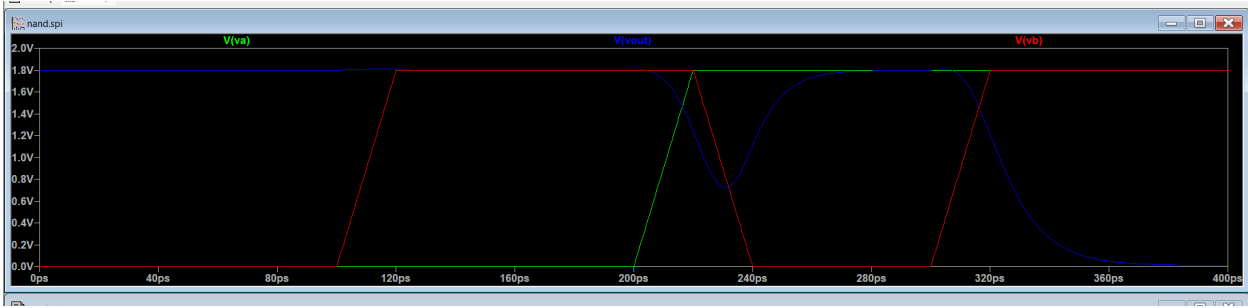
| Simulation | Avg Power Consumption |
|--------------------|-----------------------|
| Schematic | 10.87234 W |
| Layout - extracted | 10.87209 W |

- Waveform Analysis:**

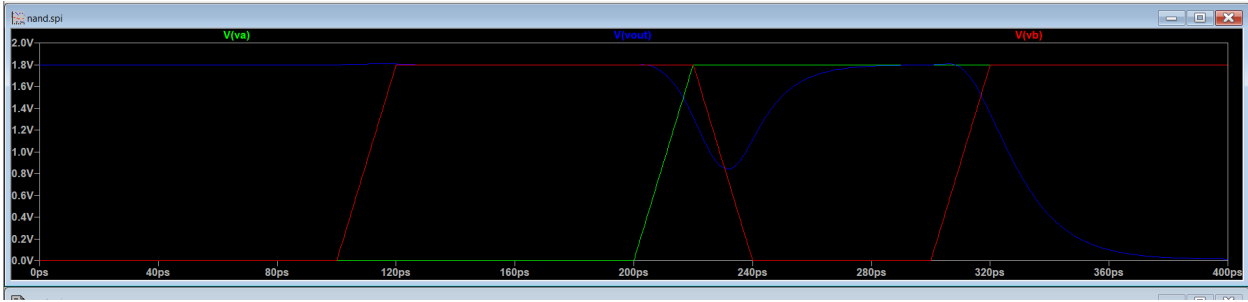
| A(Va) | B(Vb) | Y(Vout) |
|-------|-------|---------|
| 0 | 0 | 1 |
| 0 | 1 | 1 |
| 1 | 0 | 1 |
| 1 | 1 | 0 |

C=5fF

Schematic:

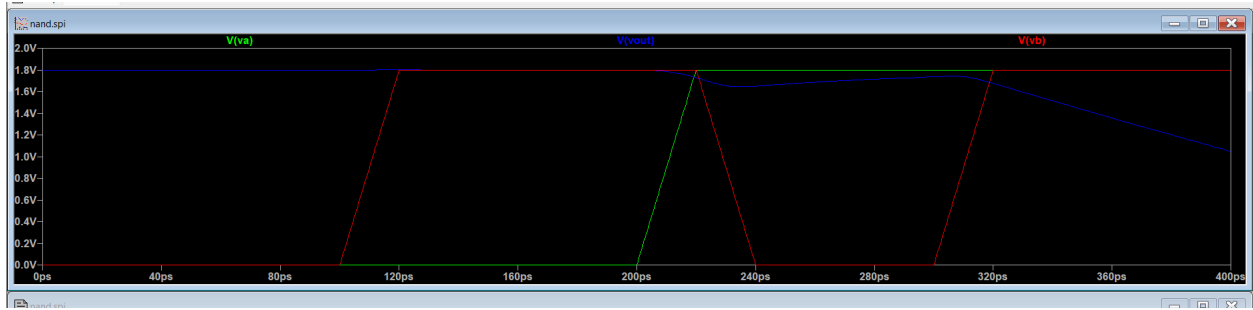


Layout:

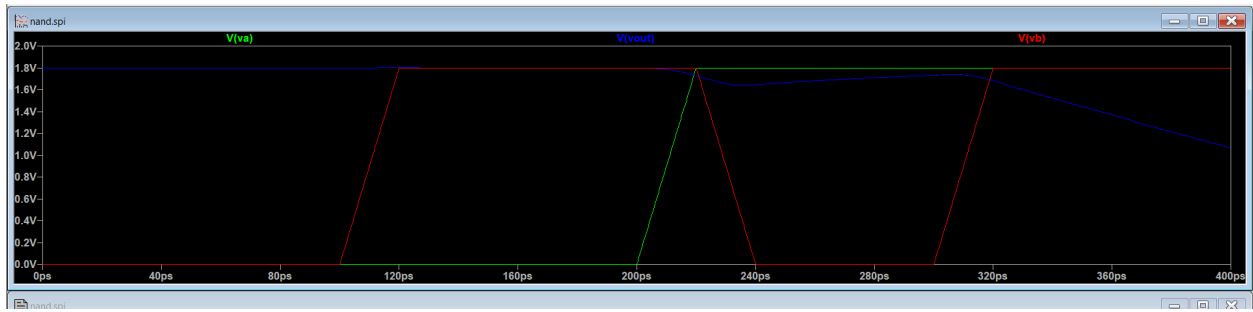


C=50fF

Schematic:

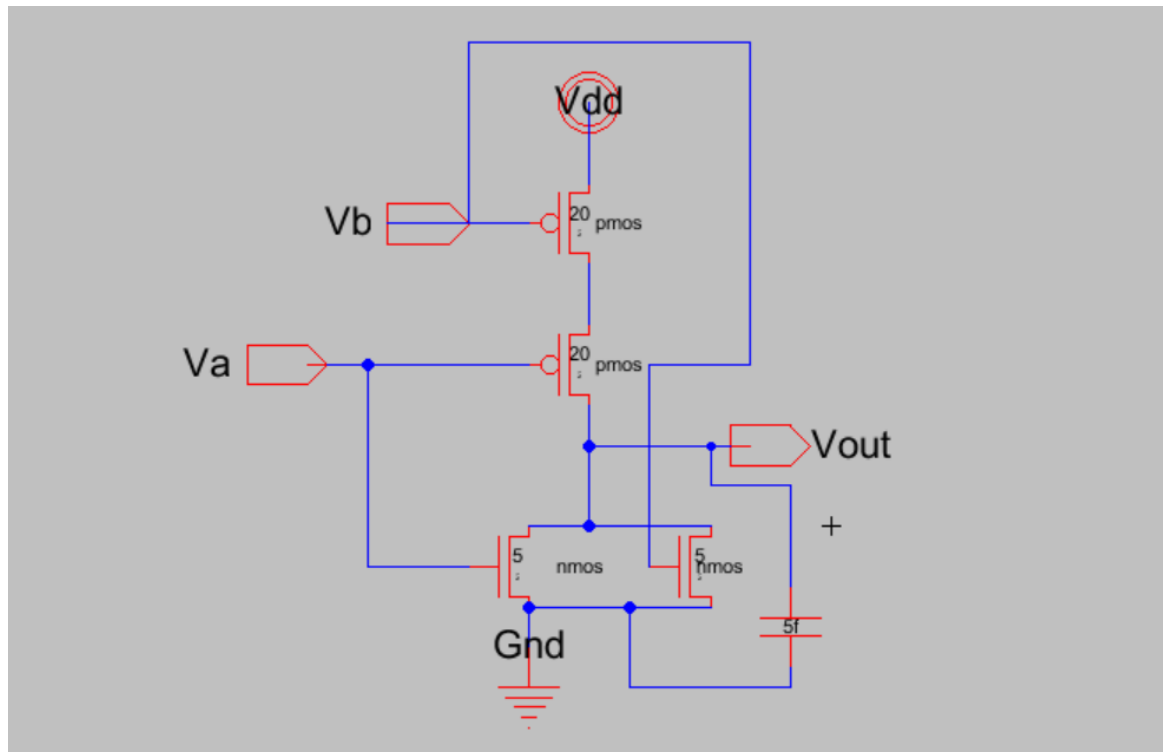


Layout:



3. Third standard cell : 2-input NOR gate

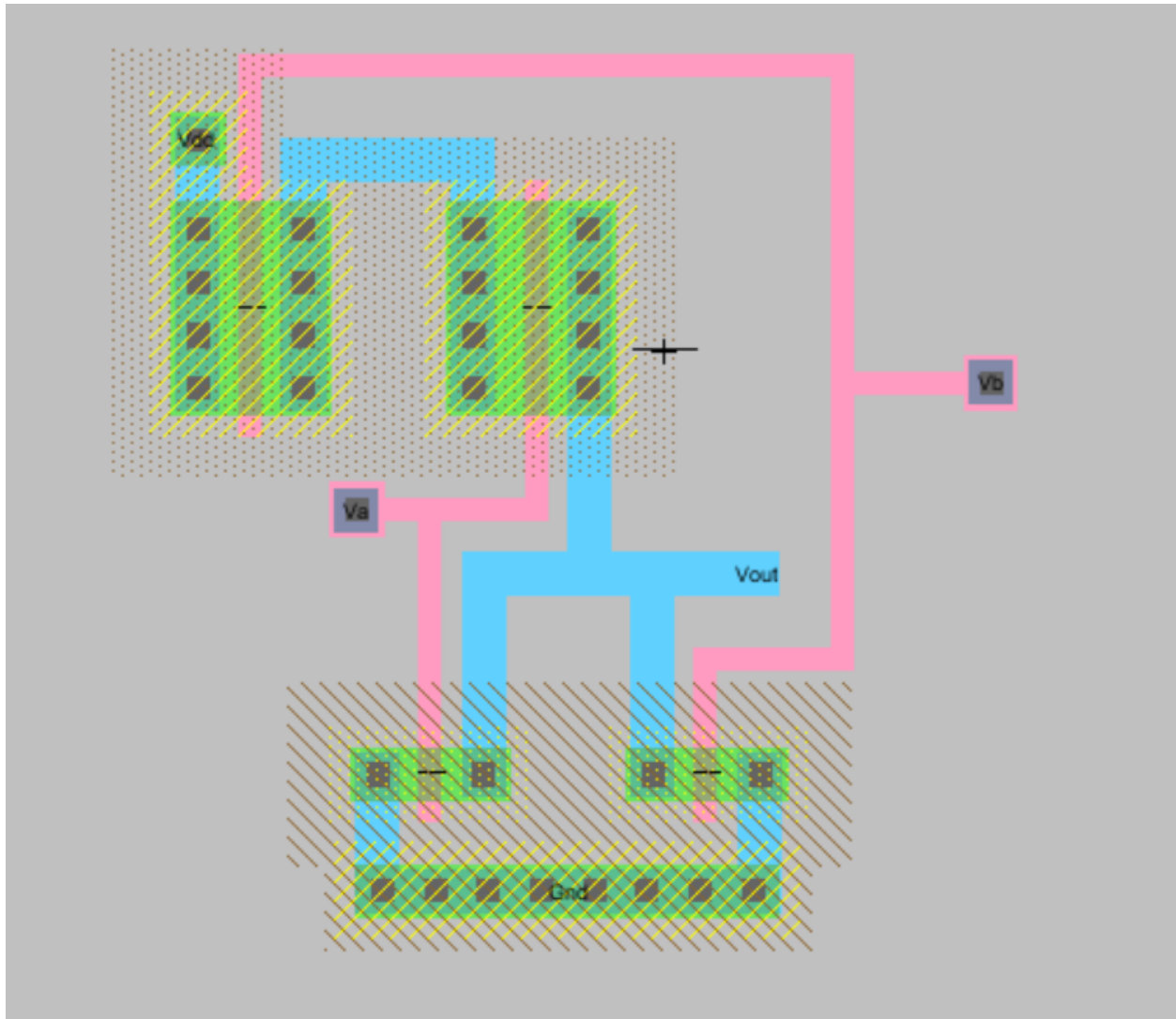
- Screenshot of the schematic

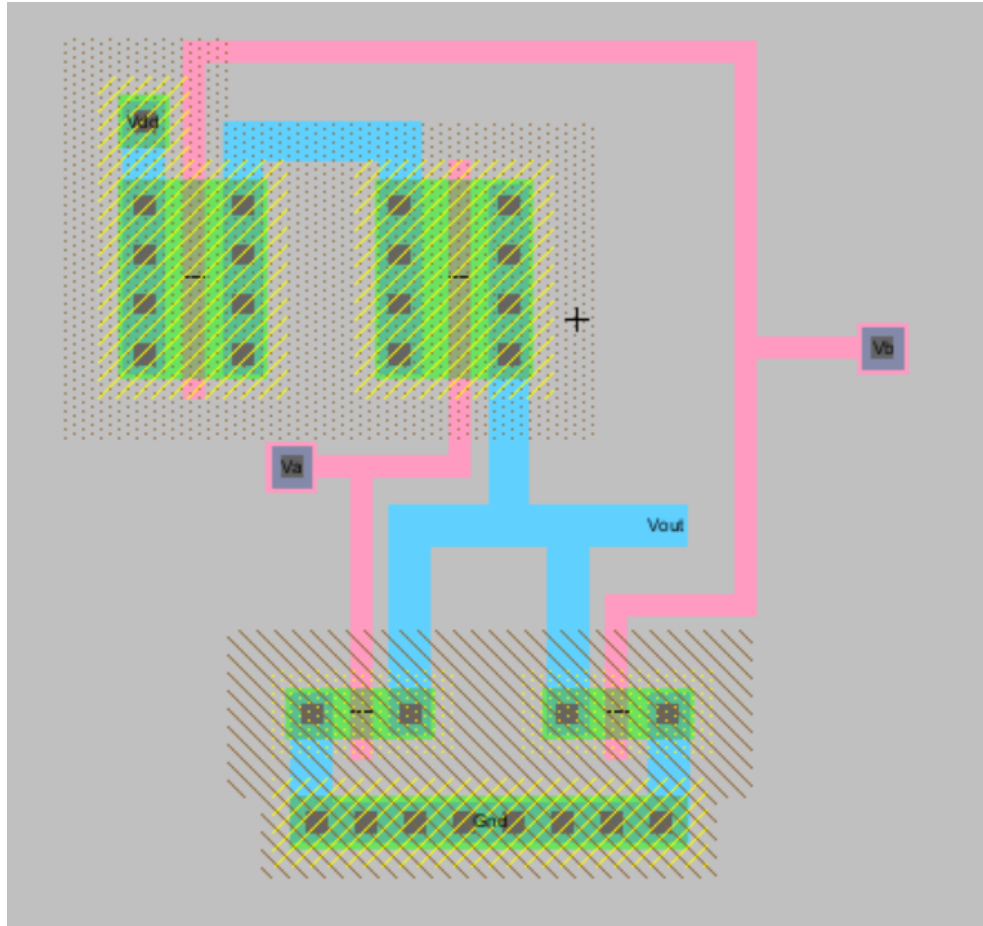


- **Explanation on how the transistor sizes were chosen**

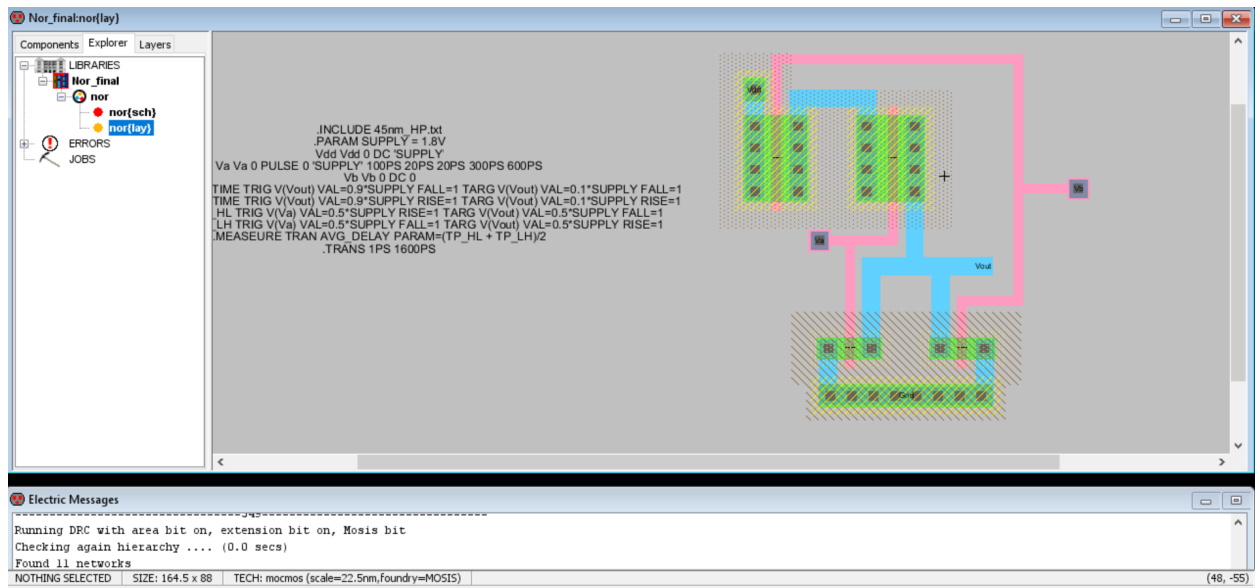
Here, the size of pmos is 20λ & size of nmos is 5λ . Two pmos of 20λ in series provide resistance equal to 10λ size pmos. Two nmos of size 5λ will provide worst-case resistance equal to that of 5λ size nmos. If we look at final equivalent sizes, they came up to a ratio of 2:1 (PUN:PDN)

- Screenshot of Layout

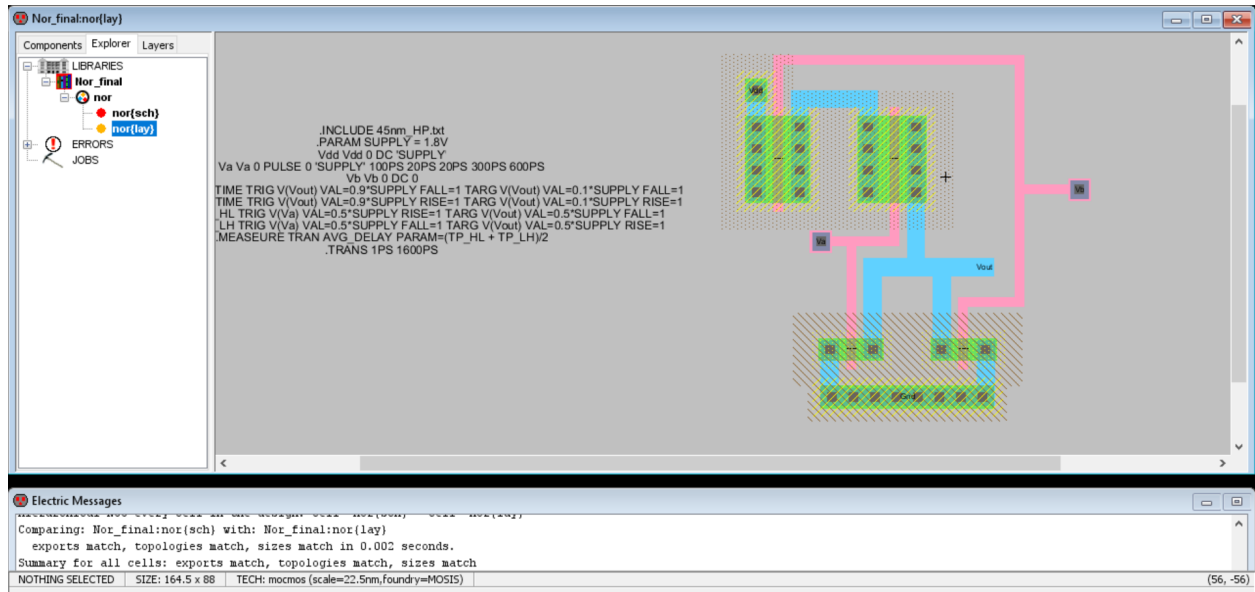




- Screenshot of layout with DRC log:



- Screenshot of Layout with LVS log:



Size of Circuit = 164.5 x 88 nm (At the bottom part of the simulation)

- Table with the propagation delay values from the schematic and the layout for 5 fF and 50 fF fanout loads

| Capacitor | Propagation delay(Schematic) | Propagation delay(Layout) |
|-----------|------------------------------|---------------------------|
| 5fF | 1.47e-11 s | 1.66e-11 s |
| 50fF | 1.03e-10 s | 1.04e-10 s |

- the power consumption from the schematic and layout-extracted simulations :

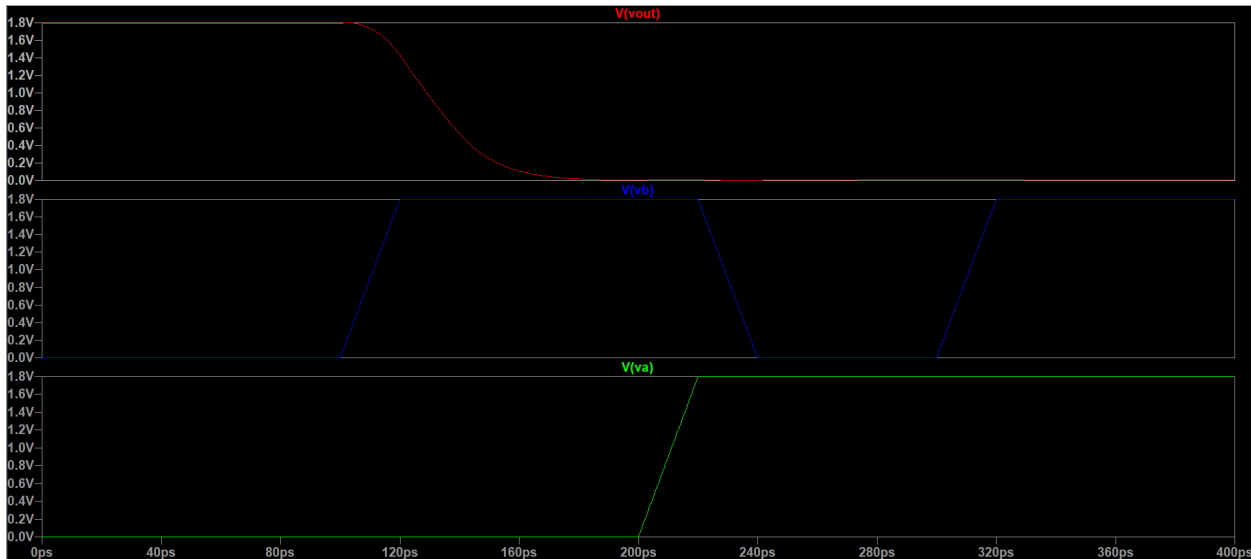
| Simulation | Avg Power Consumption |
|--------------------|-----------------------|
| Schematic | 10.92508 W |
| Layout - extracted | 10.93279 W |

Vdd =1.8 V

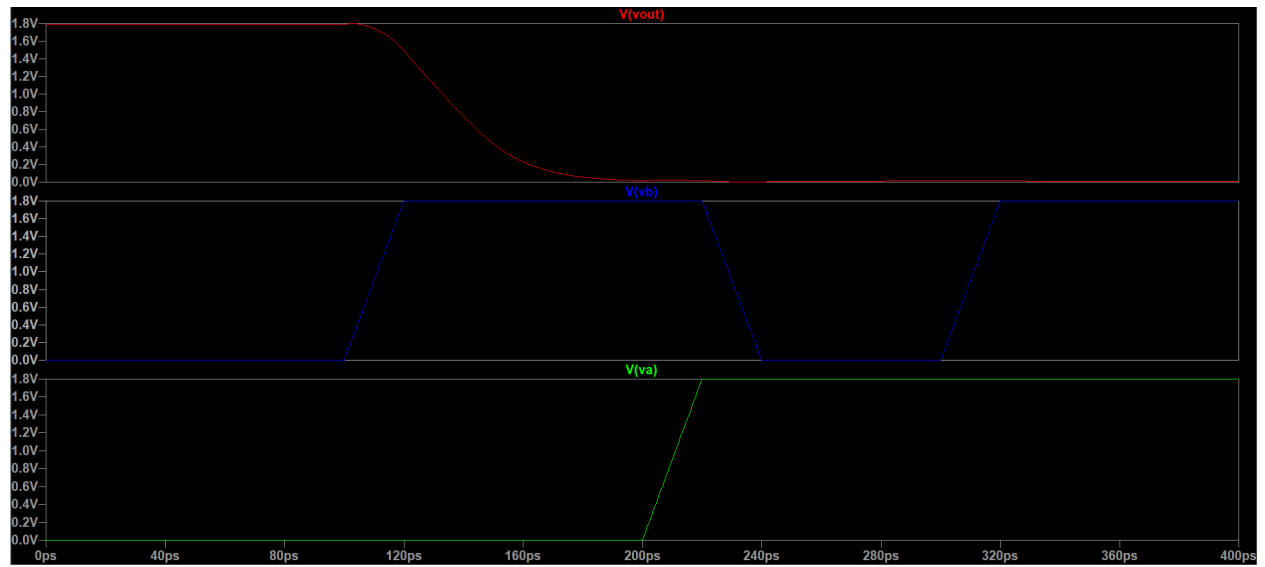
Wavefrom Analysis:

| A(Va) | B(Vb) | Y(Vout) |
|-------|-------|---------|
| 0 | 0 | 1 |
| 0 | 1 | 0 |
| 1 | 0 | 0 |
| 1 | 1 | 0 |

C=5fF:
Schematic

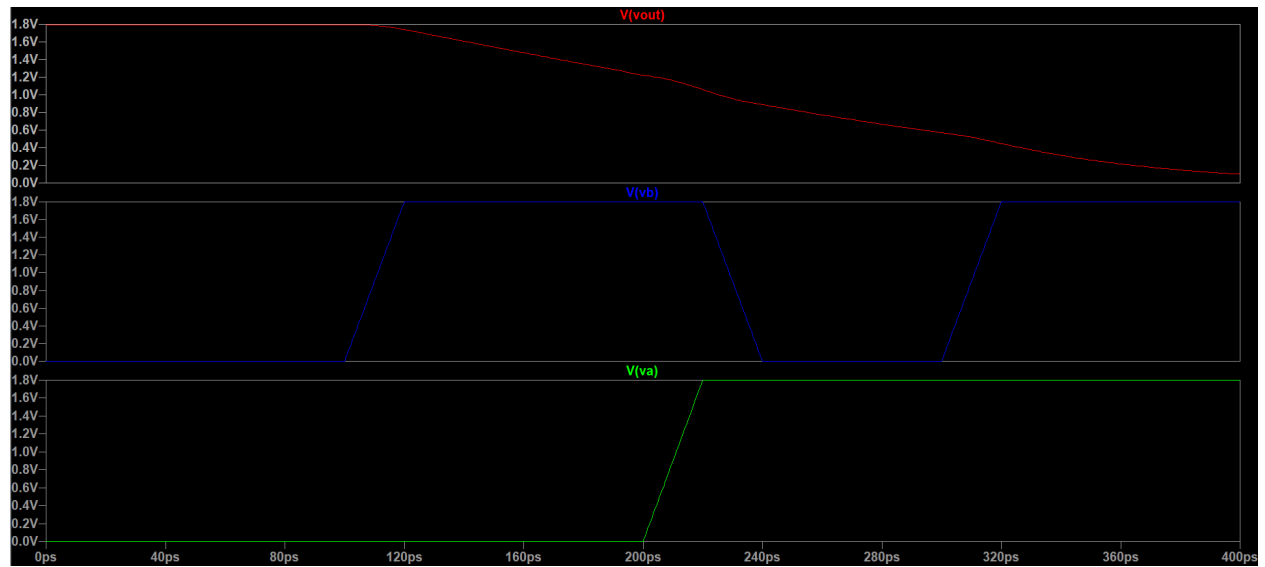


Layout:



$C=50\text{fF}$

Schematic:



Layout:

